

# Mono N-Type Silicon Wafer (G12R)

182.3x210



## Geometric Parameter

<b>Side length</b>	Short Side:182.3±0.2mm,Long Side:210±0.2mm
<b>Diagonal</b>	272±0.25mm
<b>Thickness</b>	130(+10/-8)μm
<b>Arc length projection</b>	182 Length:4.72±0.57mm 210 Length:4.07±0.52mm



## Electrical Properties

<b>Resistivity</b>	0.6-1.6Ω·cm
<b>Minority carrier</b>	≥1000μs
<b>Oxygen content</b>	≤5.75x10 <sup>17</sup> at/cm <sup>3</sup>
<b>Carbon content</b>	≤5x10 <sup>16</sup> at/cm <sup>3</sup>

## Material Properties

<b>Growth method</b>	CZ
<b>Orientation</b>	<100>±2°

## Surface Performance

<b>TTV</b>	≤20
<b>Warpage</b>	≤40
<b>Line mark</b>	≤13
<b>Edge collapse</b>	Depth≤0.3mm, length≤0.5mm, no more than one places
<b>Cracks and perforations</b>	Invisible by visual inspection
<b>Silicon wafer surface</b>	Clean, free of oil, soap, glue and other residues